

FUKUCOM COMPANY LTD.

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FAIRCHILD SEMICONDUCTOR TH

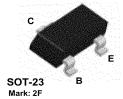
Discrete POWER & Signal **Technologies**

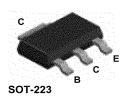
PN2907A

MMBT2907A

PZT2907A

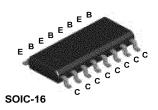


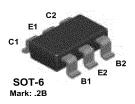




MMPQ2907

NMT2907





PNP General Purpose Amplifier

This device is designed for use as a general purpose amplifier and switch requiring collector currents to 500 mA. Sourced from Process 63.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	60	V
V _{CBO}	Collector-Base Voltage	60	V
V _{EBO}	Emitter-Base Voltage	5.0	V
Ic	Collector Current - Continuous	800	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

 $^{{}^{\}bigstar}\text{These ratings are limiting values above which the service ability of any semiconductor device may be impaired.}$

These ratings are based on a maximum junction temperature of 150 degrees C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.



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Symbol	Parameter	Test Conditions	Min	Max	Unit
OEE CHA	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	I _C = 10 mA, I _B = 0	60		l v
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 10 \text{ µA}, I_E = 0$	60		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \mu\text{A}, I_C = 0$	5.0		l v
V (BR)EBO	Base Cutoff Current	$V_{CB} = 30 \text{ V}, V_{EB} = 0.5 \text{ V}$	3.0	50	nA
	Collector Cutoff Current	$V_{CB} = 30 \text{ V}, V_{BE} = 0.5 \text{ V}$ $V_{CE} = 30 \text{ V}, V_{BE} = 0.5 \text{ V}$		50	
I _{CEX}			ļ		nA
Сво	Collector Cutoff Current	$V_{CB} = 50 \text{ V}, I_{E} = 0$ $V_{CB} = 50 \text{ V}, I_{E} = 0, T_{A} = 150^{\circ}\text{C}$		0.02 20	μA μA
	-				
ON CHAR	ACTERISTICS				
n _{FE}	DC Current Gain	I _C = 0.1 mA, V _{CE} = 10 V	75		
		$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V}$	100		
		$I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V}$	100		
		$I_{\rm C} = 150 \text{ mA}, V_{\rm CE} = 10 \text{ V}^*$	100 50	300	
	Collector-Emitter Saturation Voltage*	$I_C = 500 \text{ mA}, V_{CE} = 10 \text{ V*}$ $I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$	30	0.4	- V
V _{CE(sat)}	Collector-Entitles Gataration Voltage	$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		1.6	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 150 mA, I _B = 15 mA*		1.3	V
		I _C = 500 mA, I _B = 50 mA		2.6	V
SMALL SI	GNAL CHARACTERISTICS (except	ot MMPQ2907 and NMT2907)			
			200		MHz
	Current Gain - Bandwidth Product	$I_{\rm C} = 50 \text{ mA}, V_{\rm CE} = 20 \text{ V},$	200	1	1
f _T	Current Gain - Bandwidth Product	f = 100 MHz	200		
f _T		f = 100 MHz $V_{CB} = 10 \text{ V}, I_{E} = 0,$	200	8.0	pF
f _T C _{obo}	Current Gain - Bandwidth Product Output Capacitance	f = 100 MHz $V_{CB} = 10 \text{ V}, I_{E} = 0,$ f = 100 kHz	200		pF
	Current Gain - Bandwidth Product	f = 100 MHz $V_{CB} = 10 \text{ V}, I_{E} = 0,$	200	8.0	
f _T C _{obo}	Current Gain - Bandwidth Product Output Capacitance	$ f = 100 \text{ MHz} $ $V_{CB} = 10 \text{ V, } I_E = 0, $ $f = 100 \text{ kHz} $ $V_{EB} = 2.0 \text{ V, } I_C = 0, $	200		pF
C _{obo}	Current Gain - Bandwidth Product Output Capacitance	$\begin{split} &f = 100 \text{ MHz} \\ &V_{\text{CB}} = 10 \text{ V, I}_{\text{E}} = 0, \\ &f = 100 \text{ kHz} \\ &V_{\text{EB}} = 2.0 \text{ V, I}_{\text{C}} = 0, \\ &f = 100 \text{ kHz} \end{split}$	200		pF
f _T C _{obo} C _{ibo} SWITCHII	Current Gain - Bandwidth Product Output Capacitance Input Capacitance	$\begin{split} &f = 100 \text{ MHz} \\ &V_{\text{CB}} = 10 \text{ V, I}_{\text{E}} = 0, \\ &f = 100 \text{ kHz} \\ &V_{\text{EB}} = 2.0 \text{ V, I}_{\text{C}} = 0, \\ &f = 100 \text{ kHz} \end{split}$	200		pF
f _T C _{obo} C _{ibo} SWITCHII	Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS (except MN	$\begin{aligned} f &= 100 \text{ MHz} \\ V_{CB} &= 10 \text{ V, } I_E = 0, \\ f &= 100 \text{ kHz} \\ V_{EB} &= 2.0 \text{ V, } I_C = 0, \\ f &= 100 \text{ kHz} \end{aligned}$ IPQ2907 and NMT2907)	200	30	pF pF
T C _{obo} C _{ibo} SWITCHII	Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS (except MN Turn-on Time	$\begin{split} f &= 100 \text{ MHz} \\ V_{CB} &= 10 \text{ V, } I_E = 0, \\ f &= 100 \text{ kHz} \\ V_{EB} &= 2.0 \text{ V, } I_C = 0, \\ f &= 100 \text{ kHz} \\ \end{split}$ $V_{CB} &= 2.0 \text{ V, } I_{C} = 0, \\ V_{CB} &= 2.0 \text{ V, } I_{C} = 0, \\ V_{CB} &= 3.0 \text{ V, } I_{C} = 150 \text{ mA,} \end{split}$	200	30	pF pF
Gobo Cibo SWITCHII	Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS (except MN Turn-on Time Delay Time	$\begin{split} f &= 100 \text{ MHz} \\ V_{CB} &= 10 \text{ V, } I_E = 0, \\ f &= 100 \text{ kHz} \\ V_{EB} &= 2.0 \text{ V, } I_C = 0, \\ f &= 100 \text{ kHz} \\ \end{split}$ $V_{CB} &= 2.0 \text{ V, } I_{C} = 0, \\ V_{CB} &= 2.0 \text{ V, } I_{C} = 0, \\ V_{CB} &= 3.0 \text{ V, } I_{C} = 150 \text{ mA,} \end{split}$	200	30 45 10	pF pF
F _T C _{obo}	Current Gain - Bandwidth Product Output Capacitance Input Capacitance NG CHARACTERISTICS (except MN Turn-on Time Delay Time Rise Time	$\begin{split} &f=100 \text{ MHz} \\ &V_{CB}=10 \text{ V, } I_{E}=0, \\ &f=100 \text{ kHz} \\ &V_{EB}=2.0 \text{ V, } I_{C}=0, \\ &f=100 \text{ kHz} \\ \end{split}$ $V_{EB}=2.0 \text{ V, } I_{C}=0, \\ &f=100 \text{ kHz} \\ \end{split}$ $IPQ2907 \text{ and } NMT2907)$ $V_{CC}=30 \text{ V, } I_{C}=150 \text{ mA, } \\ &I_{B1}=15 \text{ mA} \end{split}$	200	30 45 10 40	pF pF ns ns ns

^{*}Pulse Test: Pulse Width £ 300 ms, Duty Cycle £ 2.0%

Spice Model

PNP (ls=650.6E-18 Xti=3 Eg=1.11 Vaf=115.7 Bf=231.7 Ne=1.829 lse=54.81f lkf=1.079 Xtb=1.5 Br=3.563 Nc=2 lsc=0 lkr=0 Rc=.715 Cjc=14.76p Mjc=.5383 Vjc=.75 Fc=.5 Cjc=19.82p Mjc=.3357 Vjc=.75 Tr=111.3n Tf=603.7p ltf=.65 Vtf=5 Xtf=1.7 Rb=10)



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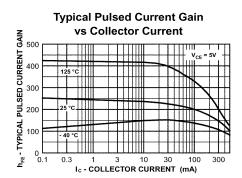
Thermal Characteristics TA = 25°C unless otherwise noted

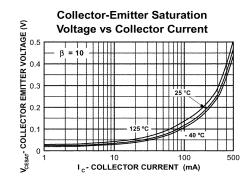
Symbol	Characteristic	Max		Units
		PN2907A	*PZT2907A	
P _D	Total Device Dissipation Derate above 25°C	625 5.0	1,000 8.0	mW mW/°C
R _{eJC}	Thermal Resistance, Junction to Case	83.3		°C/W
R _{0JA}	Thermal Resistance, Junction to Ambient	200	125	°C/W

Symbol	Characteristic	Max		Units
		**MMBT2907A	MMPQ2907	
P _D	Total Device Dissipation	350	1,000	mW
	Derate above 25°C	2.8	8.0	mW/°C
R _{0JA}	Thermal Resistance, Junction to Ambient	357		°C/W
	Effective 4 Die		125	°C/W
	Each Die		240	°C/W

^{*}Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm².

Typical Characteristics





^{**}Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."



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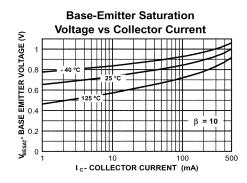
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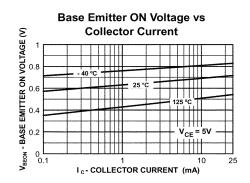
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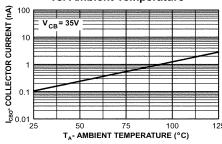
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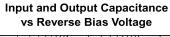
Typical Characteristics (continued)

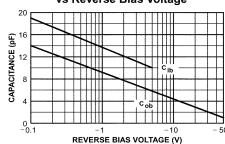




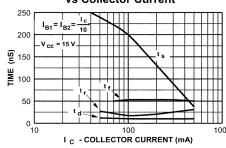
Collector-Cutoff Current vs. Ambient Temperature



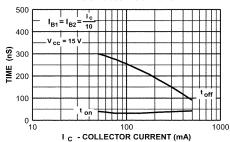








Turn On and Turn Off Times vs Collector Current





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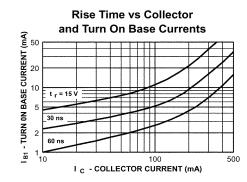
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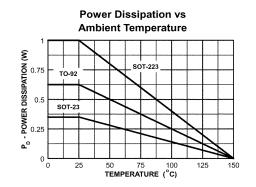
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(continued)

Typical Characteristics (continued)





Test Circuits

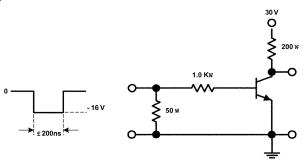


FIGURE 1: Saturated Turn-On Switching Time Test Circuit

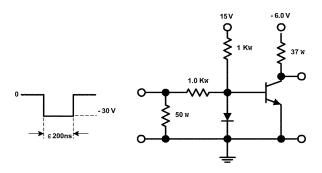


FIGURE 2: Saturated Turn-Off Switching Time Test Circuit



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